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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>[Signature]</i>	Sameshima et al., "XeCl excimer laser annealing used to fabricate poly-si TFTs", Mat. Res. Soc. Symp. Proc., Vol. 71, 1986, pp. 435-440
<i>[Signature]</i>	Corey et al., "A shallow junction submicrometer PMOS process without high temperature anneals", IEEE electron device letters, Vol. 9, No. 10, Oct. 1988, pp. 542-544
<i>[Signature]</i>	"Fabrication of Submicrometer MOSFET's Using Gas Immersion Laser Doping (GILD)", IEEE Electron Device Letters, Vol. EDL-7, No. 7, pp. 440-442

Examiner G. MUNSON Date Considered 30 DECEMBER 1997